# MMBD2837LT1G, MMBD2838LT1G, SMMBD2837LT1G

# Monolithic Dual Switching Diodes

#### Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS (EACH DIODE)

Rating	Symbol	Value	Unit
Peak Reverse Voltage	V <sub>RM</sub>	75	Vdc
D.C. Reverse Voltage MMBD2837LT1G, SMMBD2837LT1G MMBD2838LT1G	V <sub>R</sub>	30 50	Vdc
Peak Forward Current	I <sub>FM</sub>	450 300	mAdc
Average Rectified Current	Ι <sub>Ο</sub>	150 100	mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^{\circ}C$	PD	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance,	$R_{\theta JA}$		°C/W
Junction-to-Ambient		556	
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^{\circ}C$	PD	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance,	$R_{\theta JA}$		°C/W
Junction-to-Ambient		417	
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	–55 to +150	°C

1. FR–5 = 1.0  $\times$  0.75  $\times$  0.062 in.

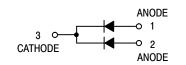
2. Alumina = 0.4  $\times$  0.3  $\times$  0.024 in. 99.5% alumina.



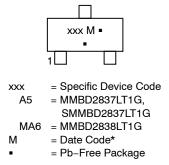
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#### MARKING DIAGRAM



(Note: Microdot may be in either location) \*Date Code orientation and/or overbar may vary depending upon manufacturing location.

## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MMBD2837LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SMMBD2837LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBD2838LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

+ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

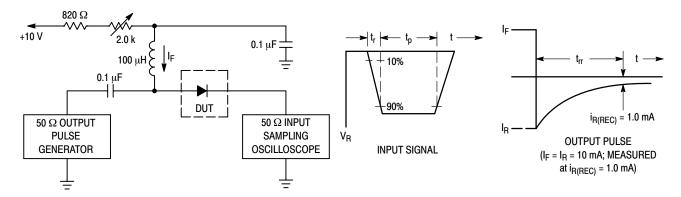
## MMBD2837LT1G, MMBD2838LT1G, SMMBD2837LT1G

#### **ELECTRICAL CHARACTERISTICS (EACH DIODE)** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit

OFF CHARACTERISTICS				
Reverse Breakdown Voltage (I <sub>(BR)</sub> = 100 μAdc) MMBD2837LT1G, SMMBD2837LT1G	V <sub>(BR)</sub>	35	_	Vdc
MMBD2838LT1G		75	-	
Reverse Voltage Leakage Current (Note 3.) (V <sub>R</sub> = 30 Vdc)	I <sub>R</sub>			μAdc
MMBD2837LT1G, SMMBD2837LT1G (V <sub>B</sub> = 50 Vdc)		-	0.1	
MMBD2838LT1G		-	0.1	
Diode Capacitance (V <sub>R</sub> = 0 V, f = 1.0 MHz)	CT	-	4.0	pF
Forward Voltage	V <sub>F</sub>			Vdc
$(I_F = 10 \text{ mAdc})$		-	1.0	
(I <sub>F</sub> = 50 mAdc) (I <sub>F</sub> = 100 mAdc)		-	1.0 1.2	
Reverse Recovery Time (I <sub>F</sub> = I <sub>R</sub> = 10 mAdc, I <sub>R(REC)</sub> = 1.0 mAdc) (Figure 1)	t <sub>rr</sub>	-	4.0	ns

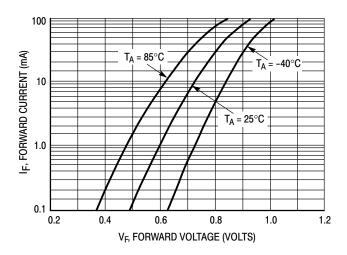
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 3. For each individual diode while the second diode is unbiased.



Notes: 1. A 2.0 k $\Omega$  variable resistor adjusted for a Forward Current (I<sub>F</sub>) of 10 mA. Notes: 2. Input pulse is adjusted so I<sub>R(peak)</sub> is equal to 10 mA. Notes: 3. t<sub>p</sub> » t<sub>rr</sub>

Figure 1. Recovery Time Equivalent Test Circuit

CURVES APPLICABLE TO EACH CATHODE





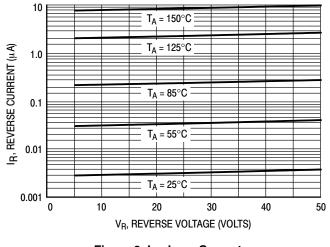


Figure 3. Leakage Current

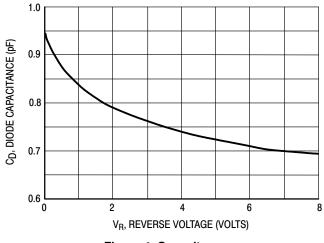


Figure 4. Capacitance





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